



LED525-36

- Green LED
- 525 nm, 9 mW
- Chip: InGaN, 350 x 350 μm
- 3 mm Clear Molding, Epoxy Resin
- Viewing Angle: 50°



Description



LED525-01 contains one InGaN LED chip die mounted on a lead frame hermetically sealed with a clear epoxy lens.

On forward bias, it emits a power radiation of typical **9 mW** at a peak wavelength at **525 nm**.

Maximum Ratings ($T_{\text{CASE}}=25^{\circ}\text{C}$)

Parameter	Symbol	Values		Unit
		Min.	Max.	
Power Dissipation	P_D		200	mW
Forward Current	I_F		50	mA
Pulse Forward Current *1	I_{FP}		100	mA
Reverse Voltage	V_F		5	V
Thermal Resistance	R_{THJA}		270	K/W
Junction Temperature	T_J		120	$^{\circ}\text{C}$
Operating Temperature	T_{CASE}	- 40	+ 100	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	- 40	+ 100	$^{\circ}\text{C}$
Lead Solder Temperature *2	T_{SLD}		+ 265	$^{\circ}\text{C}$

*1 duty=1%, pulse width = 10 μs

*2 must be completed within 3 seconds

Electro-Optical Characteristics ($T_{\text{CASE}}=25^{\circ}\text{C}$)

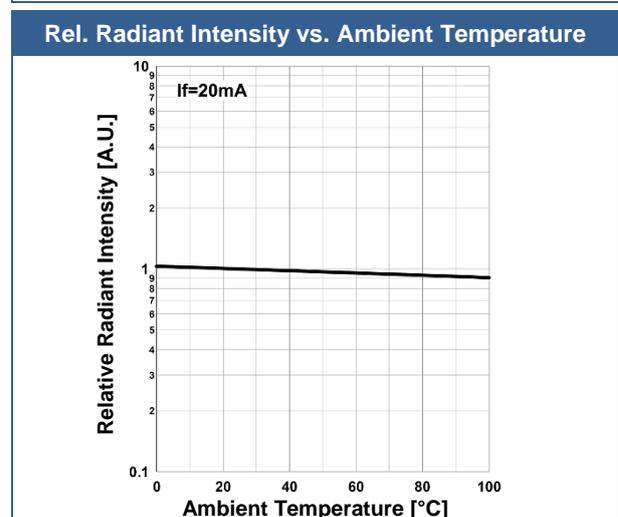
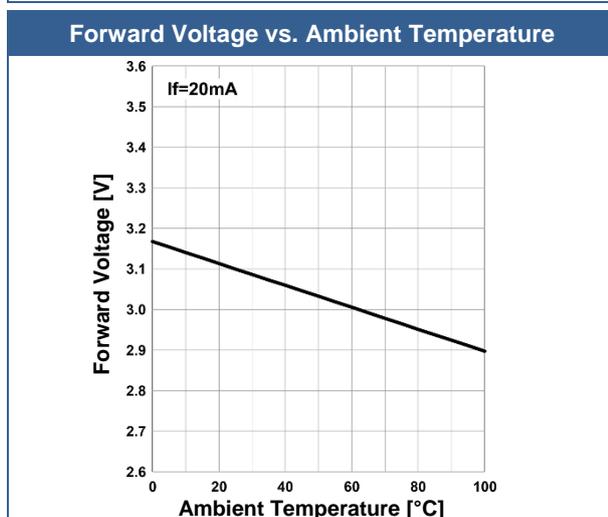
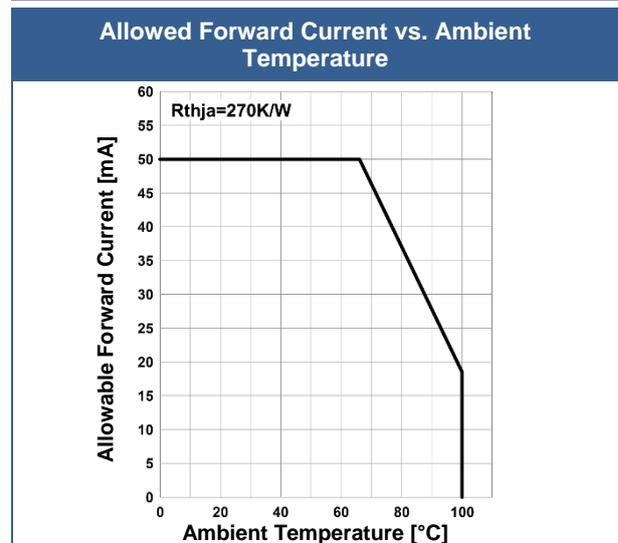
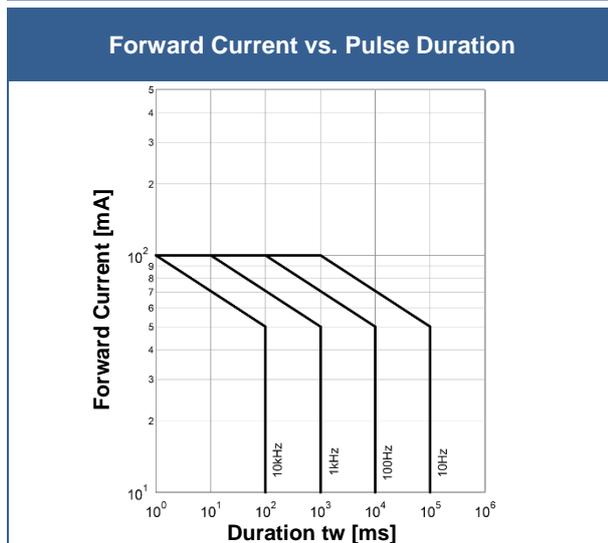
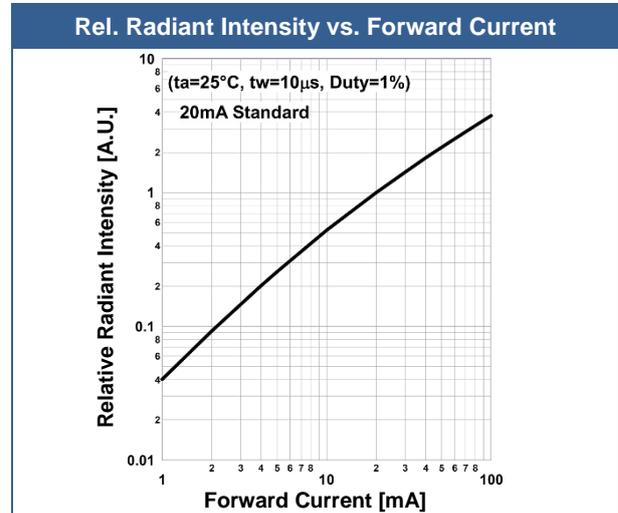
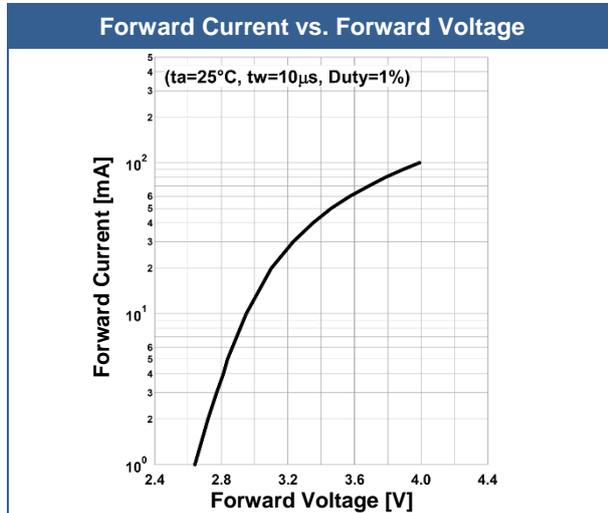
Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Peak Wavelength	λ_P	$I_F=20\text{mA}$	515		535	nm
Dominant Wavelength	λ_D	$I_F=20\text{mA}$		535		nm
Half Width	$\Delta\lambda$	$I_F=20\text{mA}$		28		nm
Forward Voltage	V_F	$I_F=20\text{mA}$		3.1	4.0	V
	V_{FP}	$I_{FP}=100\text{mA}$		4.0		
Radiated Power *1	P_O	$I_F=20\text{mA}$		9.0		mW
		$I_{FP}=100\text{mA}$		33		
Radiant Intensity *2	I_E	$I_F=20\text{mA}$		16		mW/sr
		$I_{FP}=100\text{mA}$		60		
Luminous Flux	Φ_V	$I_F=20\text{mA}$		5400		lm
Viewing Angle	φ	$I_F=20\text{mA}$		50		deg.
Rise Time	t_R	$I_F=20\text{mA}$		25		ns
Fall Time	t_F	$I_F=20\text{mA}$		50		ns

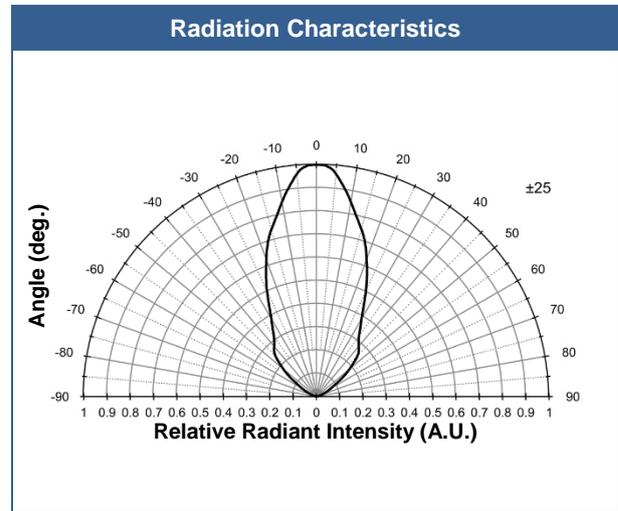
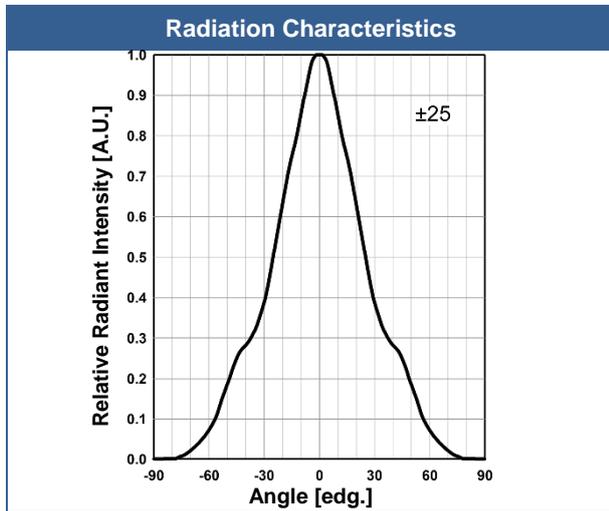
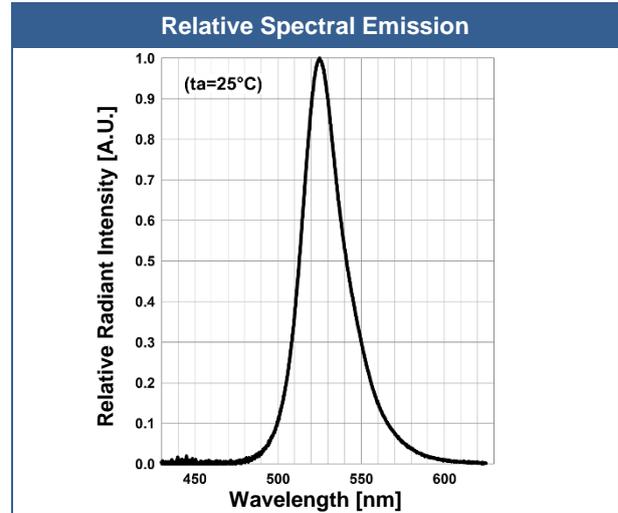
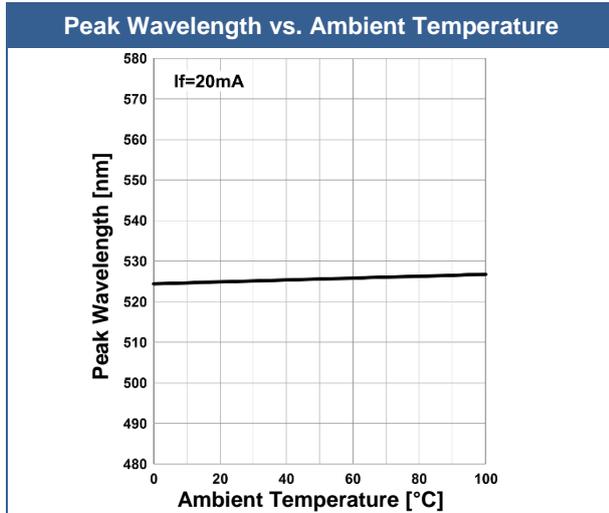
*1 measured by S3584-08

*2 measured by CIE127-2007 Condition B



Typical Performance Curves





Outline Dimensions

LED525-36
3 mm

Lead	Description
Short Pin	LED Cathode
Long Pin	LED Anode

All Dimensions in mm

